

REMARKS

1 The indication of allowability of claims 5, 8 - 12 and 23 is noted with
2 appreciation. The relevant claims have been rewritten in independent form
3 to incorporate the limitations of the base claim and intervening claims.

4 CLAIM REJECTIONS - 35 USC 103

5 The rejection of claims 1, 2, 4, 7, 15 - 16 and 19 - 22 over Chau is
6 respectfully traversed as being moot since these claims have been
7 cancelled.

8 The rejection of claims 17 and 18 over Chau is respectfully traversed.
9 Applicants point out that Chau states in paragraph 43, that the source and
10 drain regions are formed after the gate electrode is formed and that he
11 states in paragraphs 45 - 47 that the dielectric sidewall spacers are formed
12 after the source and drain regions are formed.

1 Claim 17 requires that the source and drain regions are separated from the
2 gate by the conformal insulator, which can only happen if the source and
3 drain are formed after the conformal insulator is deposited.

4 Claim 18 further requires that after the silicide process the conformal layer
5 is removed over the gate exposing a vertical surface on the gate that is
6 subject to a second silicide process, which is not shown by any of the
7 references.

8 The rejection of claims 1, 2, 4, 7, 15 - 16 and 19 - 22 over Muller is
9 respectfully traversed as being moot since these claims have been
10 cancelled.

11 The rejection of claims 17 and 18 over Muller is respectfully traversed as
12 Applicants further maintain that the combination of Chau and Muller does
13 not meet claims 17 or 18.

1 As stated above, Chau has a different sequence of steps from the claims
2 with respect to forming the source and drain before the dielectric sidewall
3 spacers are formed.


4 Applicants' attorney has not found a definite statement in Muller as to the
5 sequence of forming the source and drain and the spacers 23. Spacers 23
6 are described as nitride source drain implants, e.g. in Col. 7, line 44, which
7 indicates that the source and drain in Muller are formed by diffusion from
8 the nitride spacers 23, which means that the source and drain are defined
9 by the spacers and therefore do not meet the requirement in the
10 independent claims that the source and drain are separated from the gate by
11 the conformal insulator.

12 Further, the Muller reference does show the formation of silicide, but in
13 different locations from that of the claims.

14 With respect to claim 18, there is no showing in Muller or Chau of
15 removing the conformal layer to create an aperture and performing a
16 second silicide process in that aperture.

For the foregoing reasons, allowance of the claims is respectfully
solicited.

Respectfully submitted,

by: 
Eric W. Petraske, Attorney
Registration No. 28,459
Tel. (203) 798-1857